

*b1*

11 (Amended). A method of manufacturing a semiconductor device, comprising steps of:  
forming a semiconductor film;  
removing a contaminating impurity from the surface of the semiconductor film; and  
forming a gate insulating film in contact with the semiconductor film from the surface of  
which the contaminating impurity has been removed.

*b2*

15 (Amended). A method of manufacturing a semiconductor device, comprising steps of:  
forming at least one semiconductor island over a substrate;  
spinning the substrate by using a spinning apparatus;  
contacting an etching solution to a surface of said semiconductor island and scattering the  
etching solution during said spinning, thereby contaminating impurities are removed from the  
surface; and then  
forming a gate insulating film over said semiconductor island.

*b3*

23 (Amended). A method of manufacturing a semiconductor device, comprising steps of:  
forming gate wirings over a substrate;  
spinning the substrate by using a spinning apparatus;  
contacting an etching solution to surfaces of said substrate and said gate wirings and  
scattering the etching solution during said spinning, thereby contaminating impurities are removed  
from the surfaces; and then  
forming a gate insulating film and a semiconductor film over said gate wirings.